

Amendments To the Claims:

Please amend the claims as shown.

1. (currently amended) A Method for producing monocrystalline structures, ~~parts~~
components or workpieces, ~~in particular from metal superalloys,~~ on substrates (18),
~~in particular with a monocrystalline structure or monocrystalline structures by~~ comprising:
providing epitaxial growth;
melting a surface (11) ~~to be treated~~ of the component (6) ~~being melted~~ by an
energy input of an energy source (15) ~~by means of~~ a focal spot (3) of the energy source
(15), the focal spot having a substantially linear, elliptical or rectangular geometry;
feeding material (13) ~~being fed~~ to the molten area; and
melting the fed material (13) ~~being melted~~ completely, ~~or fed material~~
(13) ~~being melted with the surface (11), whereby it being possible for the molten material~~
is introduced to be brought into the monocrystalline structure, ~~and the molten material~~
~~being left to solidify, characterized in that the focal spot (3) has a substantially linear,~~
~~elliptical or rectangular geometry.~~
2. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the
energy input takes place by a laser (15).
3. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the
energy input takes place by electron beams.
4. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the
focal spot (3), ~~which is produced by the energy input,~~ to produce a molten area with a
substantially linear, elliptical or rectangular geometry.
5. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the
size of the focal spot (3) is changed during ~~the method~~ operation.

6. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the focal spot (3) has profile ends (5), and ~~in that~~ the intensity of the energy input is increased at the profile ends (5) as compared with the middle area of the focal spot (3).
7. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the feed of material takes place by ~~means of~~ at least one material feed (30), and ~~in that~~ the material feed is varied in terms of time and location.
8. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ wherein the temperature of the focal spot (3) is controlled.
9. (currently amended) The method as claimed in claim 1 ~~or 5~~, ~~characterized in that~~ further comprising:
moving the focal spot (3) ~~is moved~~ over the substrate (18) in a direction of advancement (4), ~~in that~~ wherein the substrate (18) has an area to which material (13) is added, ~~and in that~~, and
adapting the focal spot (3) ~~is adapted~~ to the geometry of ~~this~~ the area in such a way that a width of the focal spot (3) is adapted to the width of ~~this~~ the area transversely in relation to the direction of advancement (4).
10. (currently amended) The method as claimed in claim 1, ~~characterized in that~~ further comprising:
moving the focal spot (3) ~~is moved~~ over the substrate (18) in a direction of advancement (4), ~~in that~~ wherein the direction of advancement (4) lies in the direction of the linear extent of the surface (11) to be treated, and ~~in that~~ the energy source (15) produces a focal spot (3) the dimension of which transversely in relation to the direction of advancement (4) corresponds to the entire width of the surface (11) to be treated; and
providing a complete pass over the surface (11) to be treated for applying a coherent layer of the material (13) takes place in a single continuous advancing movement.

11. (new) The method as claimed in claim 1, wherein the monocrystalline structures, components or workpieces are produced from metal superalloys.
12. (new) The method as claimed in claim 2, further comprising:
 - moving the focal spot over the substrate in a direction of advancement wherein the substrate has an area to which material is added; and
 - adapting the focal spot to the geometry of the area such that a width of the focal spot is adapted to the width of the area transversely in relation to the direction of advancement.
13. (new) The method as claimed in claim 3, further comprising:
 - moving the focal spot over the substrate in a direction of advancement wherein the substrate has an area to which material is added; and
 - adapting the focal spot to the geometry of the area such that a width of the focal spot is adapted to the width of the area transversely in relation to the direction of advancement.
14. (new) The method as claimed in claim 1, wherein the substrate having a monocrystalline structure or monocrystalline structures.
15. (new) A method for producing monocrystalline structures, components or workpieces on substrates comprising:
 - providing epitaxial growth;
 - melting a surface of the component by an energy input of an energy source by a focal spot of the energy source the focal spot having a substantially linear, elliptical or rectangular geometry;
 - feeding material to the molten area; and
 - melting the fed material with the surface, whereby the molten material is introduced into the monocrystalline structure to solidify.

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16. (new) The method as claimed in claim 15, wherein the energy input takes place by a laser.
17. (new) The method as claimed in claim 15, wherein the energy input takes place by electron beams.
18. (new) The method as claimed in claim 15, wherein the focal spot produces a molten area with a substantially linear, elliptical or rectangular geometry.
19. (new) The method as claimed in claim 15, wherein the monocrystalline structures, components or workpieces are produced from metal superalloys.
20. (new) The method as claimed in claim 15, wherein the substrate having a monocrystalline structure or monocrystalline structures.